

Quarterly Financial Result (Supplementary Materials)

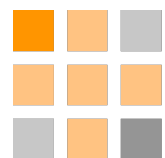
Quarter 4: three months ended
December 31, 2025

February 13, 2026
Code: 6871

Disclaimer

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Quarterly Financial Results (Q4)

Consolidated Result Summary

(Unit : Mils. of Yen)

*Amounts less than one million yen are rounded down

	FY12/2024	FY12/2025					
	Oct.-Dec.	Jul.-Sep.	Oct.-Dec.	QoQ		YoY	
	Q4 ①	Q3 ②	Q4 ③	(△) ③-②	(%)	(△) ③-①	(%)
Net Sales	16,659	17,291	19,761	+2,469	+14.3%	+3,101	+18.6%
Probe Card	16,130	16,917	19,407	+2,490	+14.7%	+3,276	+20.3%
TE ※	528	374	353	(20)	(5.5%)	(175)	(33.1%)
Gross Profit	8,283	7,683	9,719	+2,035	+26.5%	+1,435	+17.3%
Operating profit	3,928	3,730	5,241	+1,511	+40.5%	+1,313	+33.4%
Ordinary profit	3,247	3,878	5,827	+1,949	+50.3%	+2,580	+79.5%
Net Income Attributable to Owner of Parent	3,065	2,309	4,978	+2,669	+115.6%	+1,913	+62.4%

※ : Test Equipment

Consolidated Result Summary

(Unit : Mils. of Yen)

*Amounts less than one million yen are rounded down

	FY12/2024	FY12/2025					
	Jan.-Dec.		As of Nov.11		YoY		
	Results ①	Forecast ②	Results ③	(△) ③-②	(%)	(△) ③-①	(%)
Net Sales	55,643	68,900	70,173	+1,273	+1.8%	+14,530	+26.1%
Probe Card	53,526	67,100	68,525	+1,425	+2.1%	+14,999	+28.0%
TE ※	2,116	1,800	1,648	(151)	(8.4%)	(468)	(22.1%)
Gross Profit	27,143	—	33,804	—	—	+6,661	+24.5%
Operating profit	12,572	13,800	16,542	+2,742	+19.9%	+3,970	+31.6%
Ordinary Income	12,250	13,300	17,100	+3,800	+28.6%	+4,850	+39.6%
Net Income Attributable to Owner of Parent	8,811	9,200	12,063	+2,863	+31.1%	+3,252	+36.9%
Dividend per Share(yen)	70	72	95	+23	—	+25	—

※ : Test Equipment

Summary on Results

Probe card

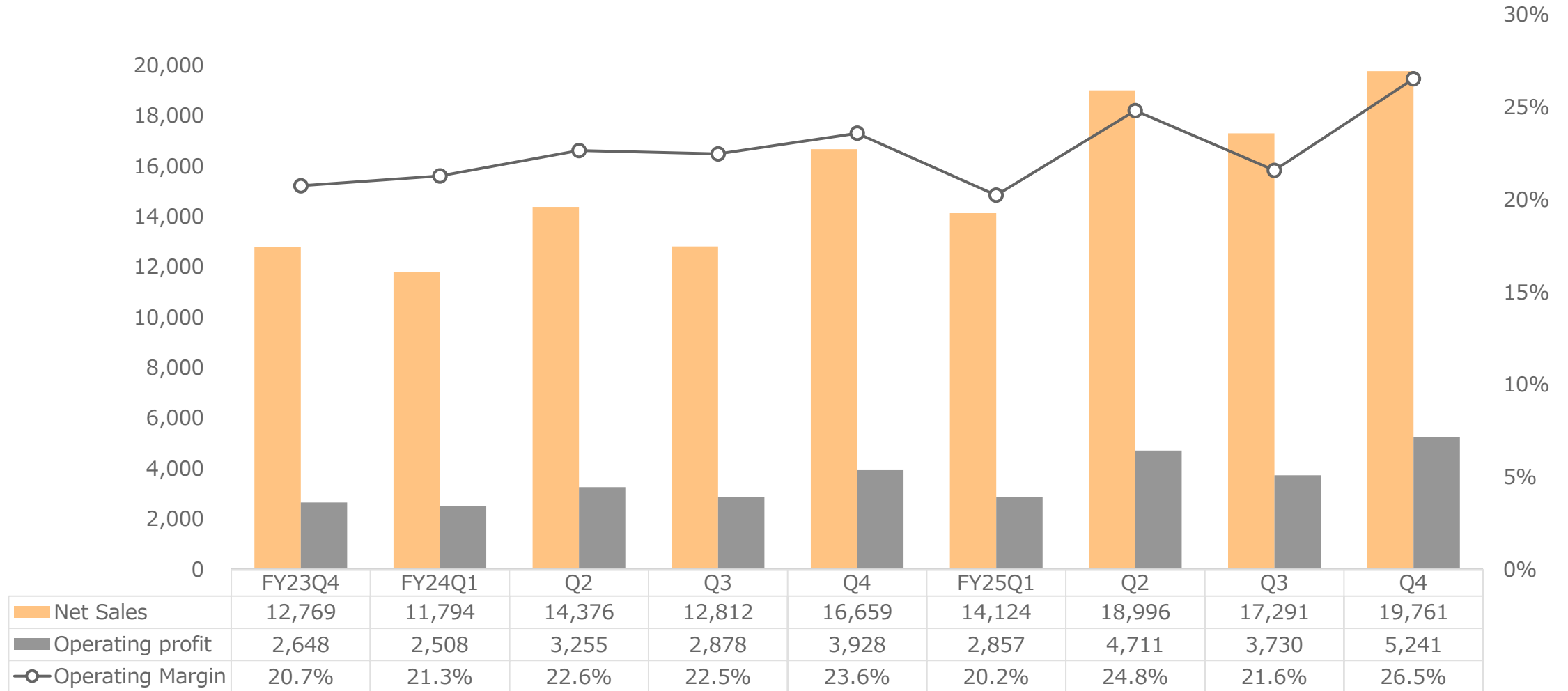
- Sales of memory probe cards reached a record high, driven by increased production capacity at the new Aomori plant, with strong growth particularly in DRAM applications.
- Orders also hit a record high, supported by robust demand for DRAM probe cards.
- Sales of non-memory probe cards declined compared to the previous quarter.
- Segment profit improved significantly from the previous quarter, reflecting strong sales growth in DRAM probe cards.

TE

- Net sales decreased from the previous quarter due to the delayed recovery in the market for semiconductor test sockets.
- The segment posted a loss.

Quarterly Financial Result

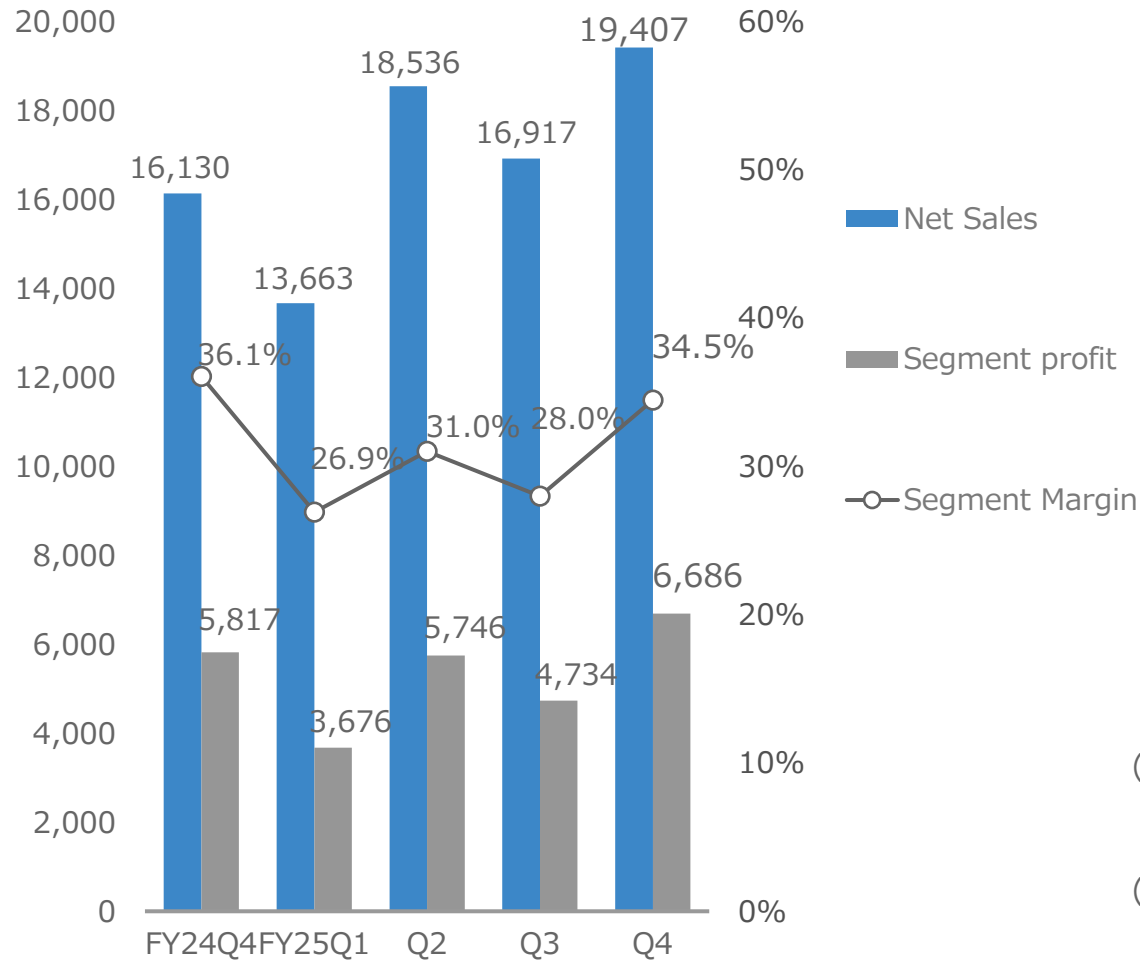
(Mils. of Yen)



Business Condition by Segment

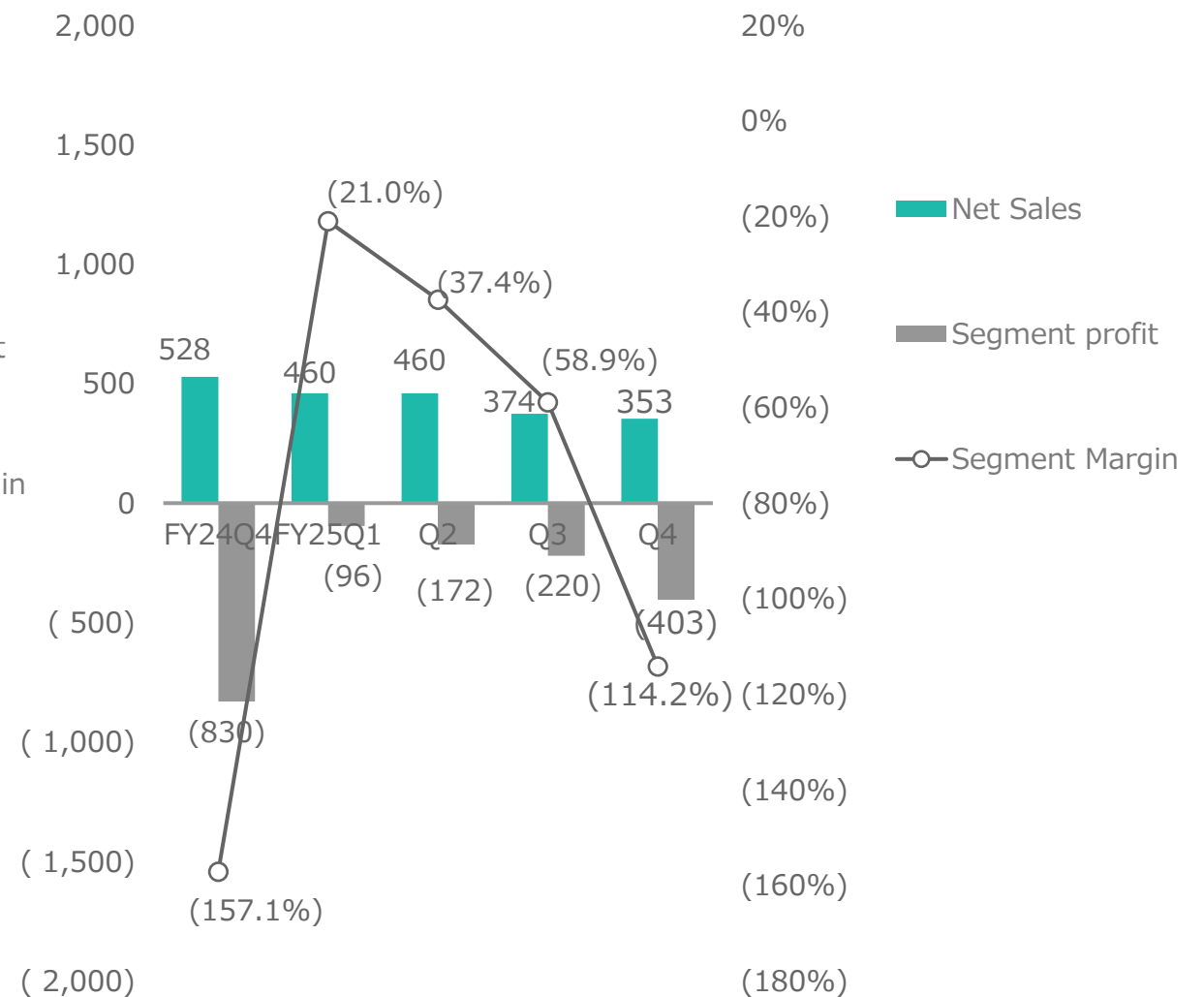
Probe card

(Mils. of Yen)



TE

(Mils. of Yen)

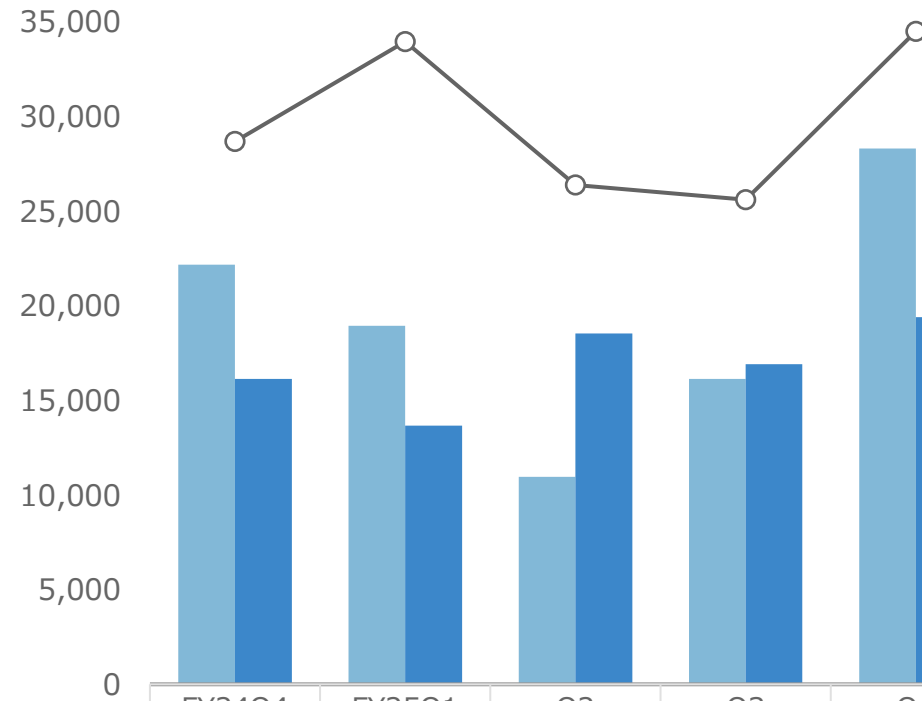


Quarterly Orders, Net Sales & Backlog

Probe card

TE

(Mils. of Yen)



(Mils. of Yen)

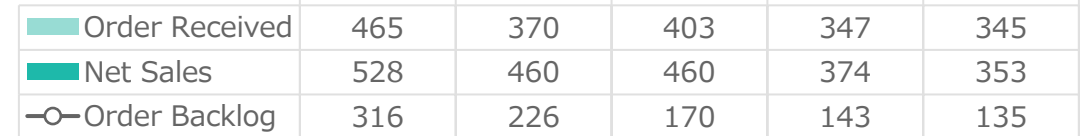
1,000

750

500

250

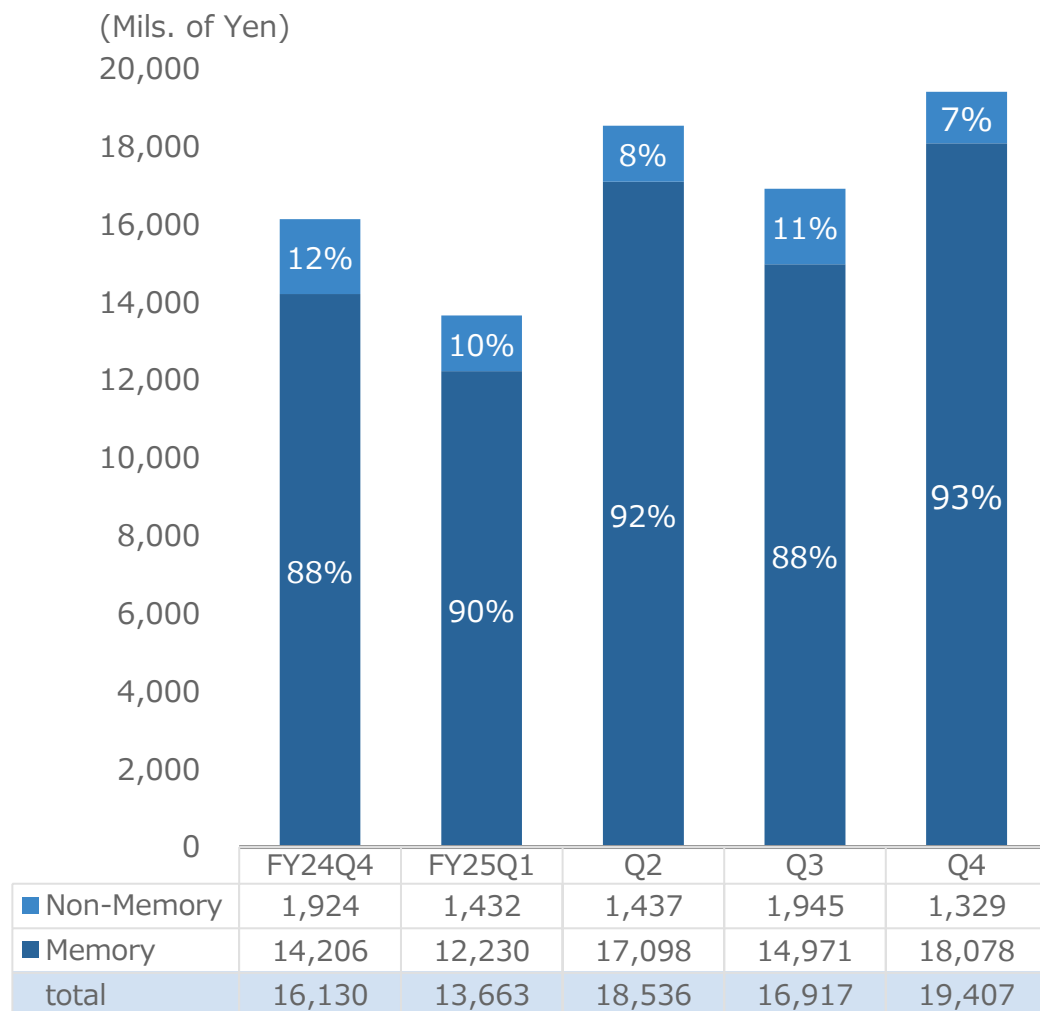
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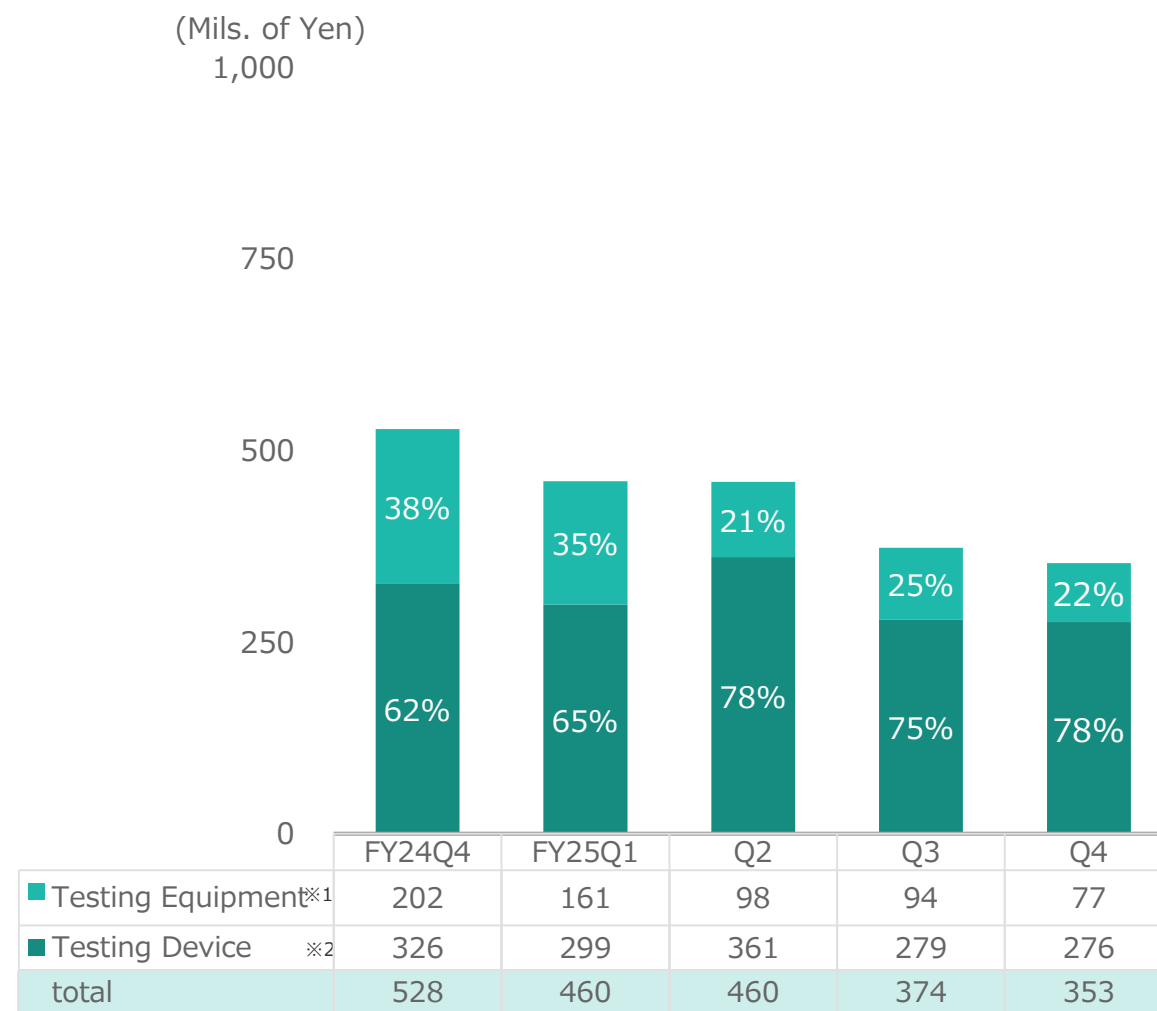
Quarterly Net Sales by Product

Probe card

TE



※ Including sales of Cantilever type

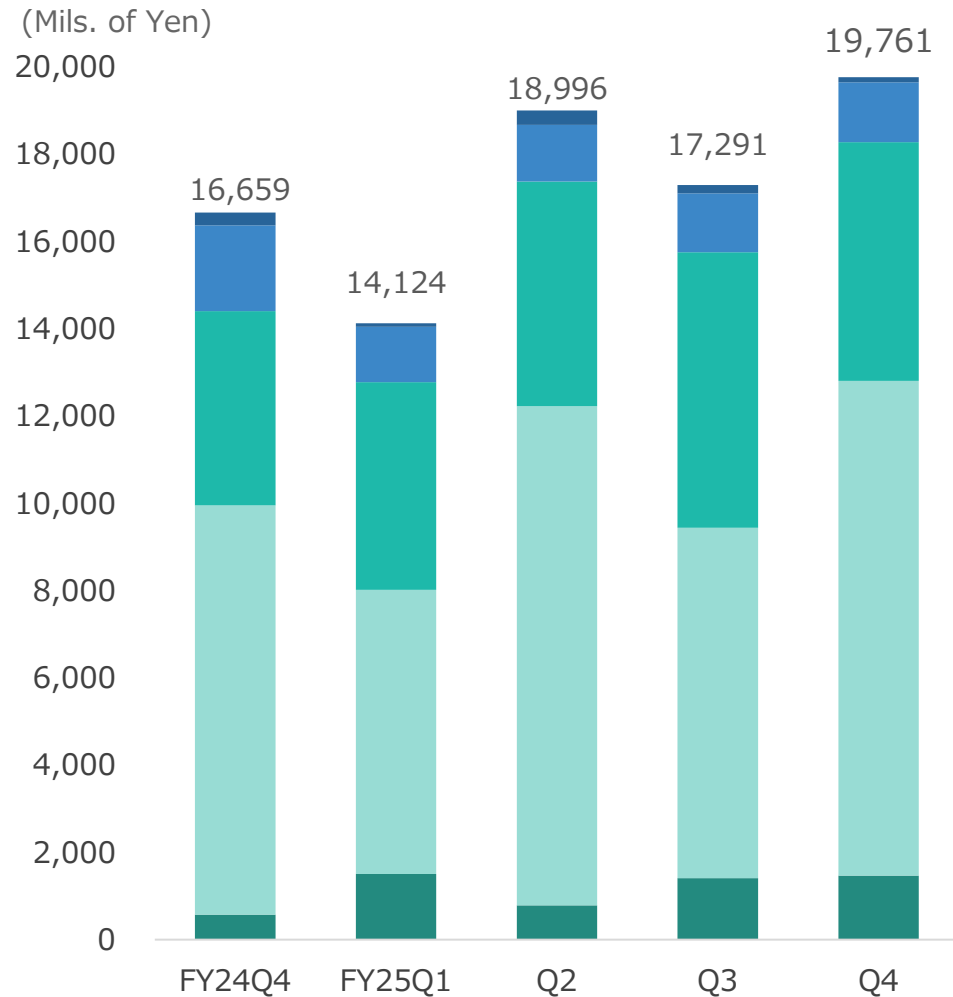


※1 Custom testers, Semiconductor probers, FPD test equipment, etc.

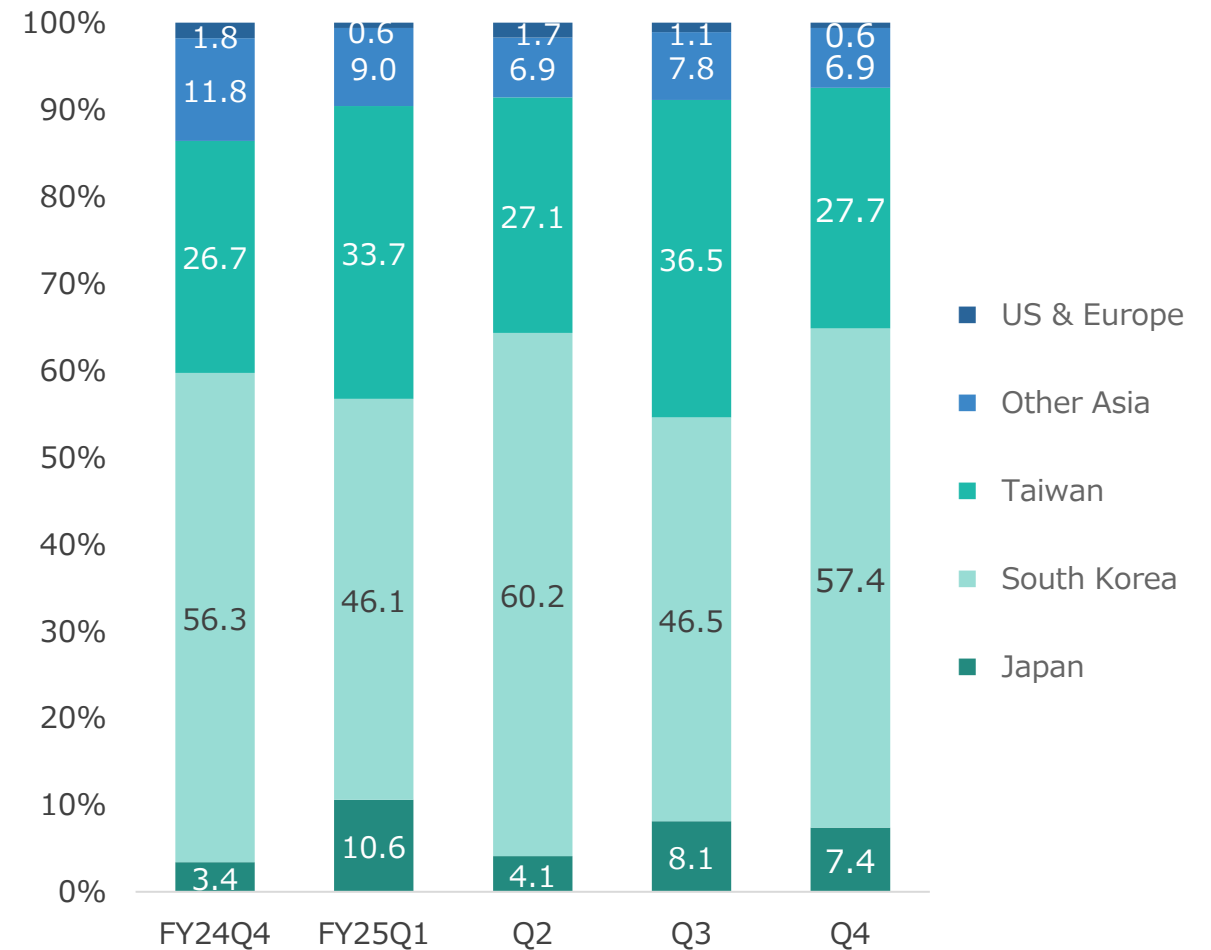
※2 Test sockets for semiconductors, Probe units for FPDs

Quarterly Net Sales by Region

Net Sales

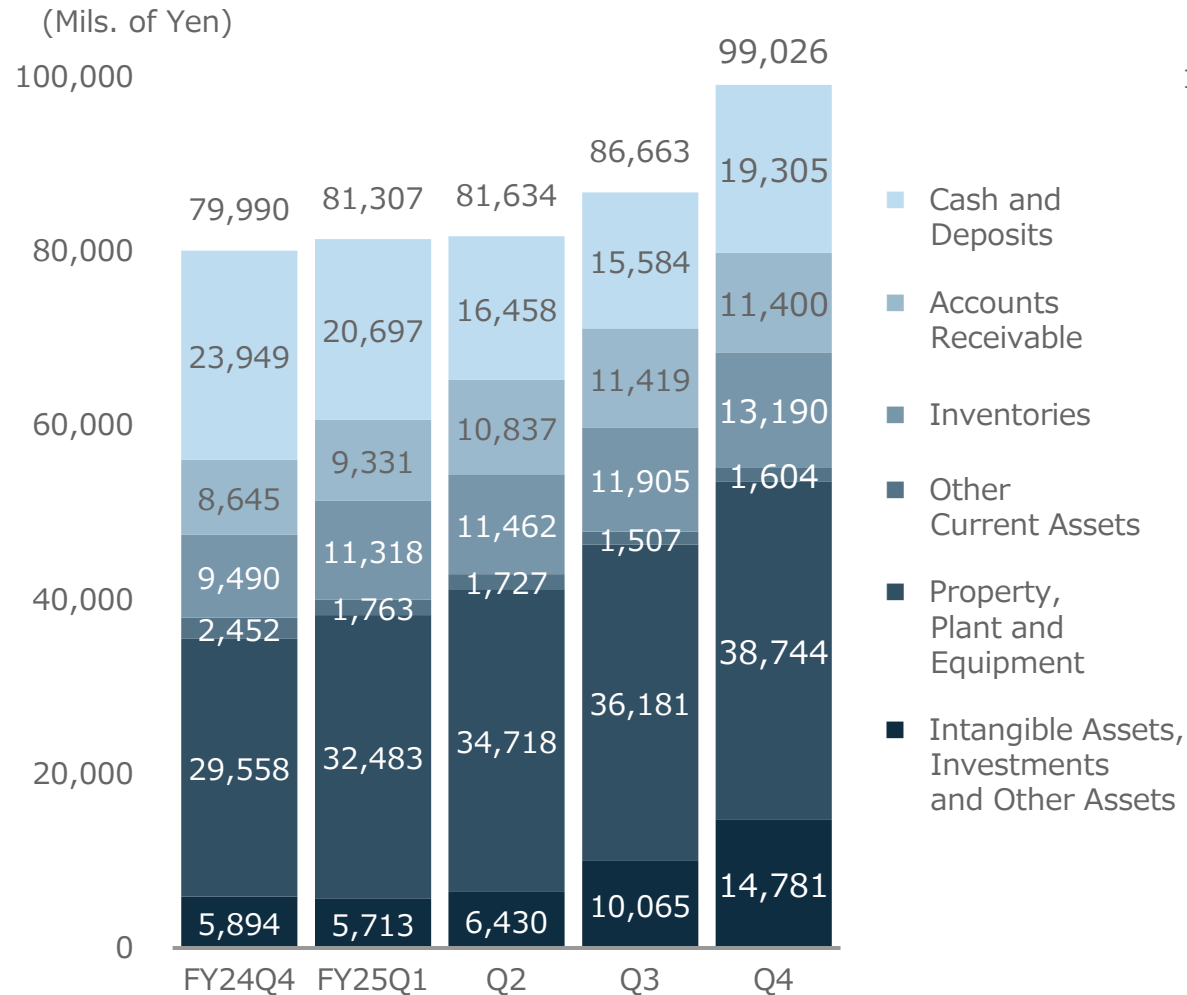


Percentage of sales

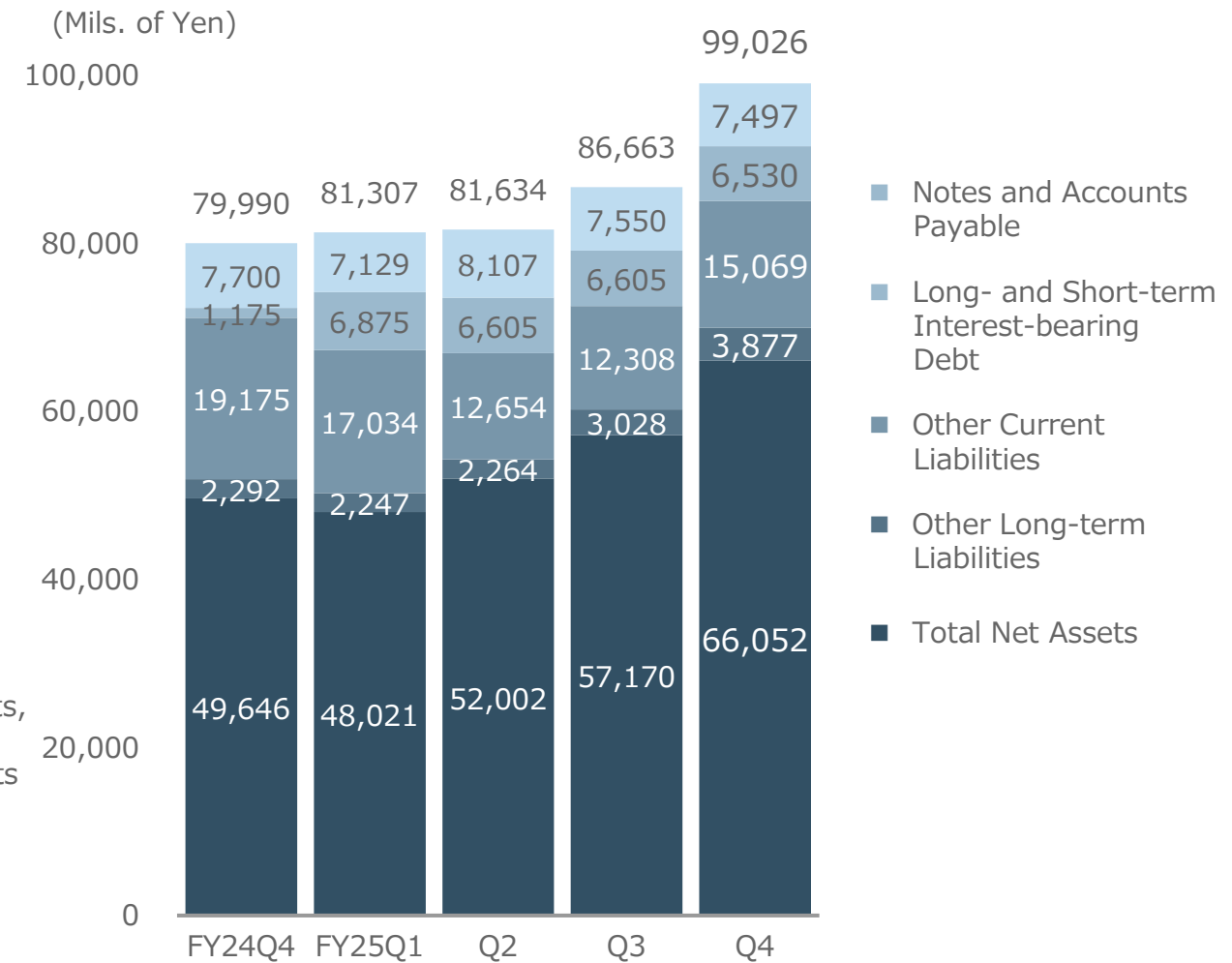


Consolidated Balance Sheet

Assets

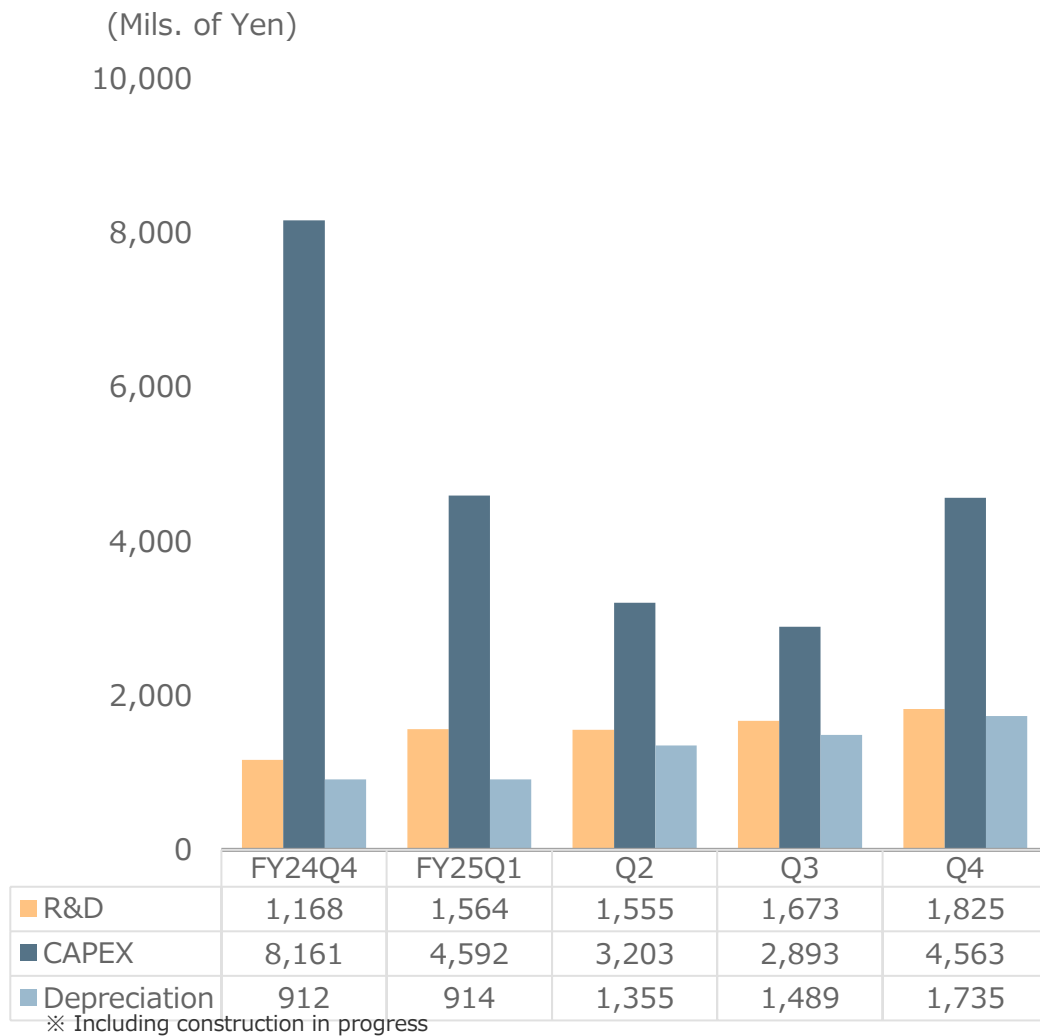


Liabilities & Net Assets

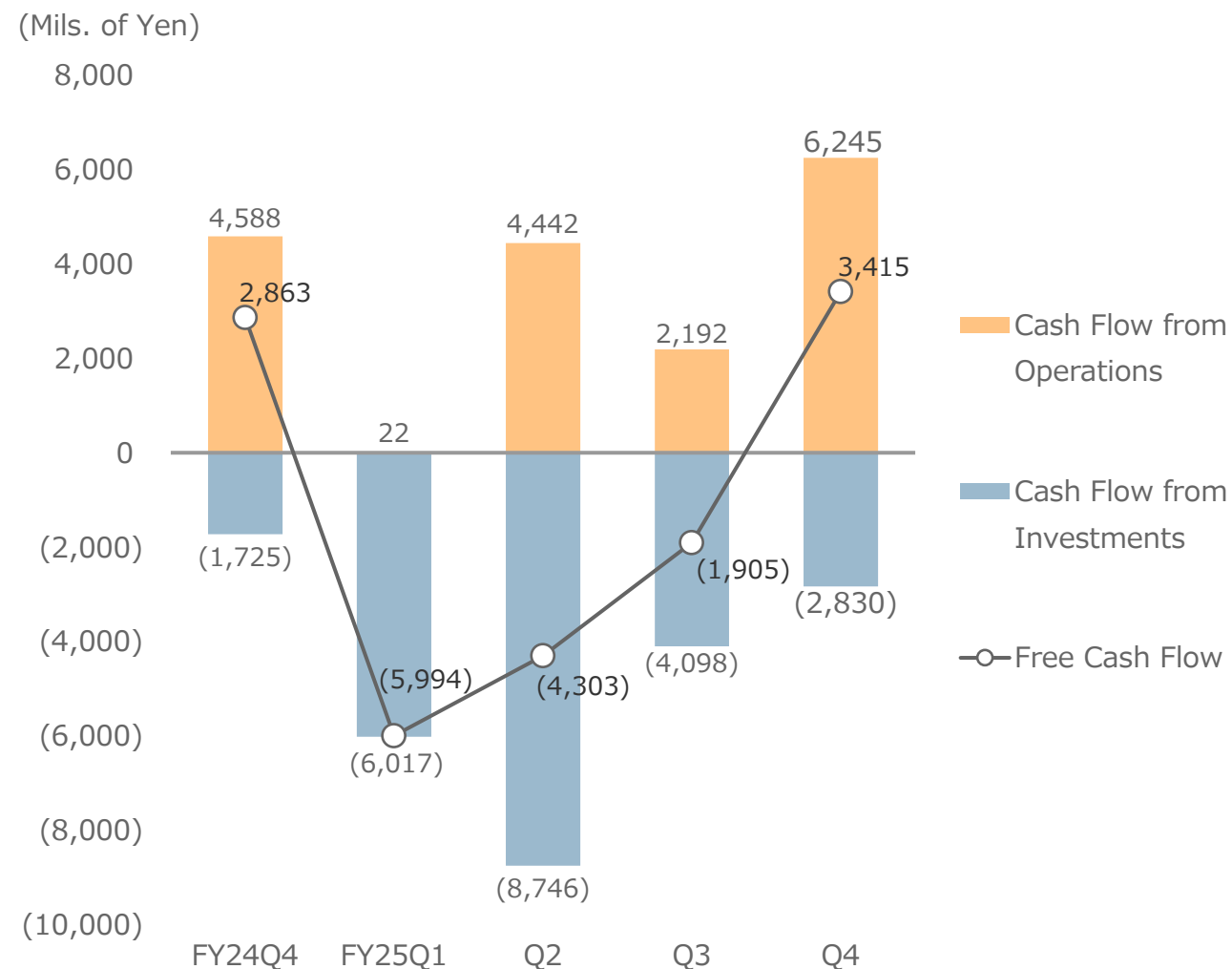


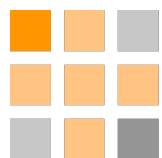
Investments/Cash Flows

Investment, etc.



Cash Flows





Forecasts

Financial Forecast

(Unit : Mils. of Yen)
*Amounts less than one million yen are rounded down

	FY12/2025	FY12/2026		
	Jan.-Jun. (Previous year)	Jan.-Jun. (New)	YoY	
	㉑	㉒	(△) ㉒-㉑	(%)
Net Sales	33,120	43,900	+10,779	+32.5%
Probe Card	32,199	43,200	+11,000	+34.2%
TE	921	700	(221)	(24.0%)
Operating profit	7,569	12,300	+4,730	+62.5%
Ordinary profit	7,394	11,800	+4,405	+59.6%
Net Income Attributable to Owner of Parent	4,774	8,200	+3,425	+71.7%

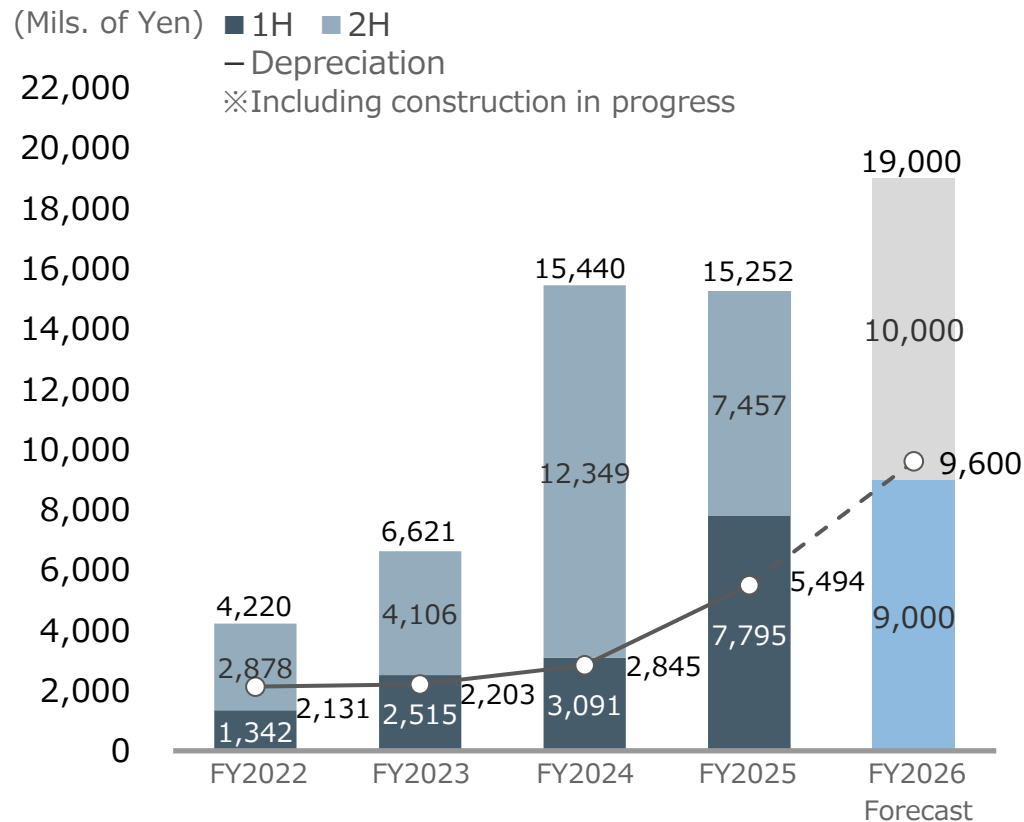
- FX rate assumption for FY12/2026: JPY 150.00 to USD, JPY 0.10 to KRW

Forecasts for R&D, Capex and Depreciation

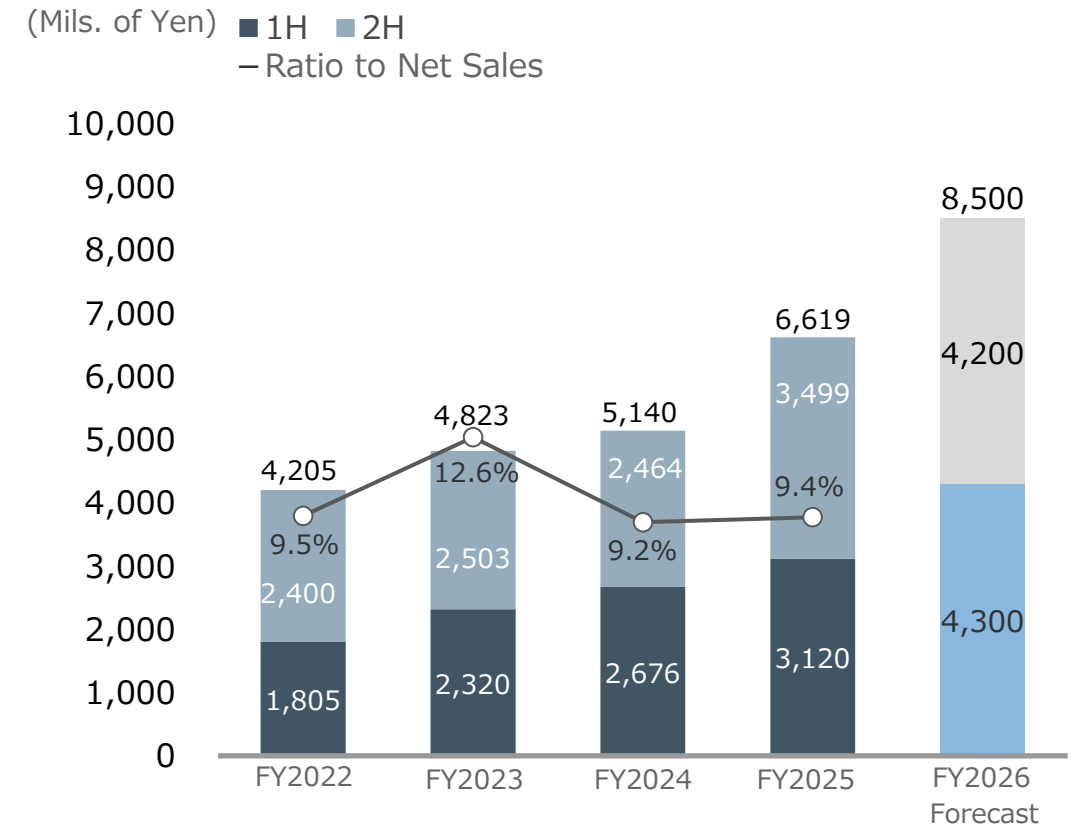
Expansion of production capacity to address mid- to long-term demand growth, and the continued investment in research and development with a view toward ongoing innovation in semiconductor technologies.

- Investment in production equipment for the new building at the Aomori Plant.
- Next-generation technology development for both non-memory and memory probe cards.
- Development of new semiconductor-related products and expansion of applications in the TE business.

Capex & Depreciation



R&D



Regarding the Sales Outlook

Starting with this earnings announcement, we will present our outlook for full-year revenue in the next fiscal year based on recent business conditions, rather than providing specific numerical forecasts.

1. Revenue Outlook

- The probe card market grew by 12% year-on-year in 2025 compared with 2024. In contrast, the Group's full-year revenue increased by 26% year-on-year, significantly outperforming overall market growth.
- For 2026, we forecast that the probe card market will grow by 14% year-on-year compared with 2025. Against this backdrop, the Group expects its full-year revenue growth to exceed the 26% growth rate achieved over the 2024–2025 period.

2. Outlook for the Mid-Term Management Plan “FV26”

In the final fiscal year of the Mid-Term Management Plan FV26, we expect revenue to exceed the management target set under the plan.

※If the actual growth rate of the probe card market falls below the Company's forecast, the outlook for full-year revenue may be adversely affected.



Glossary and Main Products

Glossary

Wafer: Circular crystalline silicon (Si) or gallium arsenide (GaAs) sliced into a thin disk substrate used for semiconductor electrical circuits.

Chip/Die: Dies and chips are small semiconductor devices. A semiconductor wafer is diced into many pieces, and each of these pieces is called a die or chip.

IC: Integrated circuit.

Memory IC: An integrated circuit made out of millions of capacitors and transistors that can store data such as DRAM, NAND Flash and etc.

Logic IC: An integrated circuit that performs logic functions.

DRAM: Dynamic random access memory.

A type of volatile memory with a wide range of uses including main storage for computers and general-purpose memory.

NAND-Type Flash Memory: A type of non-volatile memory that cannot be deleted even when the external power supply is interrupted. Used for USB memory, digital camera memory cards, mobile music players and mobile phone memory. Created by Toshiba in 1987.

LSI: Large-scale integrated circuit.

Called VLSI or ULSI when the transistor's degree of integration is increased.

Micro Computer: An IC that integrates memory and a microprocessor for arithmetic processing on one chip. Recently, the word "microcomputer" is often used to refer to those incorporated in home appliances or other products for electronic control.

System on Chip (SoC) / System LSI: Large-scale IC containing nearly an entire system on one chip. Combines multiple functions previously spread across multiple ICs onto one chip. Realizes small, high-performance machinery. Mainly used in processors and memory, input/output, interface and telecommunications circuitry.

Flip Chip: Flip chips have bump electrodes on the chip surface for the purpose of high-density surface mounting of IC chips on circuit boards. The bumps and wiring board terminals are connected with solder or conductive adhesive.

Bump: Bumps are solder bumps formed on IC pads. Bumps are normally formed with gold (Au) or solder and are used primarily in flip chips for connection to substrates.

Bonding Pad: Supply of power voltage to the chip and signal exchanges with exterior are normally conducted through the lead. The bonding pads are metal electrodes around the chip connecting this lead with each terminal on internal circuitry.

IoT: Internet of Things, allowing physical devices to be sensed or controlled remotely across existing internet infrastructure.

FPD: Flat panel display.

LCD: liquid crystal display.

Glossary

Wafer Test / Probe Test: An electrical test conducted by placing a probe needle on a wafer chip bonding pad.

Final Test / Package Test: Electrical testing of assembled ICs.

DUT: Device under test.

Area Array: A state which has test pads in a grid array on the surface of a chip.

Cantilever Probe Card: Also called a cantilever needle. A probe card using a one-sided needle probe as a fulcrum. Shaped by hand.

Advanced Probe Card: Probe cards other than the cantilever type.

Vertical Probe Cards: A vertical probe card is a probe card in which probe needles are vertical to the substrate. Vertical probe cards are suitable for area array, small pad, low voltage, low needle pressure, and high frequency measurement.

MEMS: Micro-Electro-Mechanical Systems.

MEMS Type Probe Card: MEMS type probe cards are probe cards using MEMS technology. They have a structure that allows the mechanical movement of probe terminals.

DFT: Design for testability

BIST: Built In Self Test

AI(Artificial Intelligence): The simulation of human intelligence processes by machines. It generally needs various type of semiconductors like image sensors.

Generative AI: automatically creates diverse content, including images, videos, and text. It learns from extensive pre-analyzed data, enabling the generation of new content. High-performance semiconductors like GPUs or HBMs are crucial for effective generative AI.

GPU (Graphics Processing Unit):A semiconductor chip that handles complex data calculations, including 3D graphics processing. It excels in parallel computing. When combined with HBM, it enables even faster performance, especially for generative AI.

HBM (High Bandwidth Memory) : A type of DRAM known for its wide bandwidth and high-power efficiency. By stacking DRAM chips and connecting them to a processor using multiple buses, it achieves fast and large-capacity data transfer. It is primarily packaged with GPUs/CPU and used in HPCs and AI servers.

HPC(High Performance Computing) : A technology that performs complex computational processing on massive data at high speeds. It uses high-performance processors to handle big data efficiently.

General-purpose server : A computer or program that performs necessary processing through a network in response to requests from users.

AI server: A specialized server designed specifically for training and inference of generative AI. It is equipped with powerful CPUs, GPUs, HBM, and other devices, providing higher computational capabilities, large memory storage, high bandwidth, and low latency.

Data center :A facility designed to securely store servers and network equipment. When investments in data centers increase, there is often a higher demand for general-purpose servers, which in turn can lead to an increased need for DRAM chips.

Our Products

Probe Cards






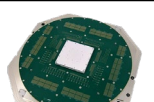
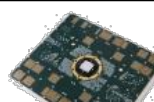
U-Probe: Our core product, realizing the world's first wafer-scale probing created with MJC's proprietary MEMS probe "micro-cantilever" and global top-level thin-film multilayer technology. With a bare minimum of contacting times via a crescent arrangement for DRAM, this product is currently the industry standard. Mainly used for memory testing on DRAM and flash memory.

SP-Probe: Vertical spring pin-type probe card suitable for 12-inch wafer batch measurements. Mainly used for testing NAND flash memory.

MEMS-V / Vertical-Probe: Vertical needle-type probe card used for testing highly integrated, high-speed multi-pin logic devices. Provides flexible support for a variety of pad and fine pitch arrangements and is suitable for multiple individual simultaneous measurements during testing of SoC and other advanced logic devices.

MEMS-SP: Probe card used for MEMS probe developed for testing SoC devices and other flip chip-type logic devices.

Main Applications for MJC Probe Card Products

	Memory		Logic	
	DRAM	Flash	SoC	
Vertical		 SP-Probe	 Vertical-Probe	 SP-Probe
MEMS	 U-Probe	 U-Probe	 MEMS-V	 MEMS-SP

Test Equipment

Semiconductor Tester: A system that gives electrical signals to a semiconductor device to compare output signals with expected values.

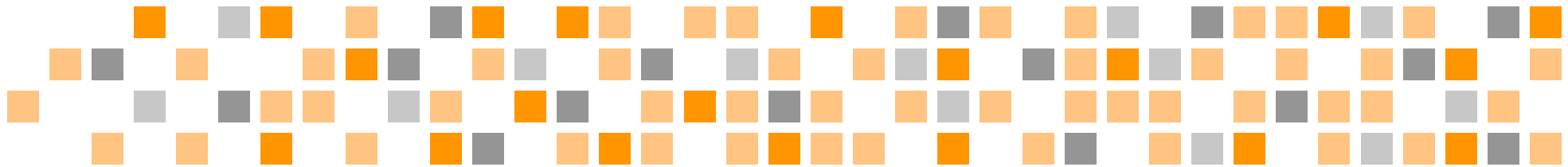
Wafer Prober: A system that handles the wafer to make contact in the designated position on the device.

Test Socket: In the final inspection of semiconductor manufacturing, a fixture is used to electrically connect the packaged device and tester. There are two types: 'J-Contacts,' suitable for high-frequency and high-performance devices, and 'BeeContacts,' which have a unique spring probe structure with excellent contact stability.

Probe Unit: Probe card with a built-in LCD prober. This blade-type unit developed by MJC is an industry standard.



MJC YOUR Best Partner, MJC Anytime Anywhere



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